

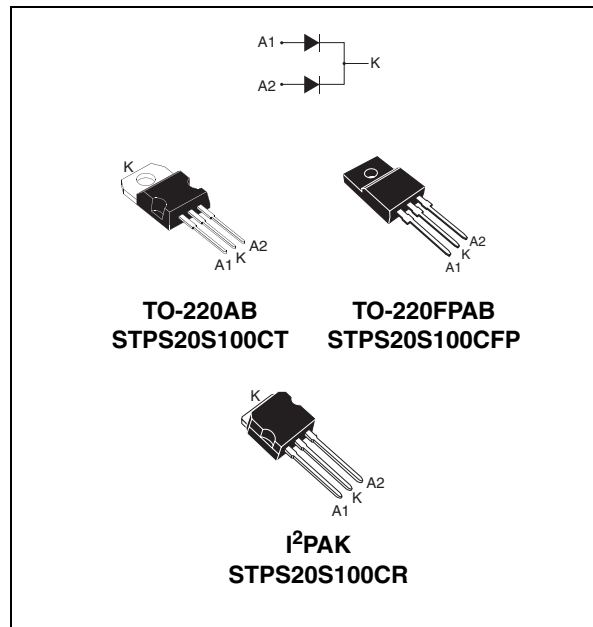
## 100 V, 20 A power Schottky rectifier

### Features

- High junction temperature capability for converters located in confined environment
- Low leakage current at high temperature
- Low static and dynamic losses as a result of the Schottky barrier
- Avalanche specification

### Description

Schottky barrier rectifier designed for high frequency miniature switched mode power supplies such as adaptators and on board dc/dc converters. The device is packaged in TO-220AB, I<sup>2</sup>PAK and TO-220FPAB.



**Table 1. Device summary**

Symbol	Value
$I_{F(AV)}$	2 x 10 A
$V_{RRM}$	100 V
$T_j$	175 °C
$V_F(max)$	0.71 V

# 1 Characteristics

**Table 2. Absolute ratings (limiting values, per diode)**

Symbol	Parameter			Value	Unit	
$V_{RRM}$	Repetitive peak reverse voltage			100	V	
$I_{F(RMS)}$	Forward rms current			30	A	
$I_{F(AV)}$	Average forward current $\delta = 0.5$	TO-220AB / I <sup>2</sup> PAK	$T_c = 150\text{ }^\circ\text{C}$	Per diode Per device	10 20	A
		TO-220FPAB	$T_c = 140\text{ }^\circ\text{C}$	Per diode Per device	10 20	
$I_{FSM}$	Surge non repetitive forward current		$t_p = 10\text{ms}$ sinusoidal	180	A	
$P_{ARM}$	Repetitive peak avalanche power		$t_p = 1\mu\text{s}$ $T_j = 25\text{ }^\circ\text{C}$	7200	W	
$T_{stg}$	Storage temperature range			-65 to + 175	$^\circ\text{C}$	
$T_j$	Maximum operating junction temperature <sup>(1)</sup>			175	$^\circ\text{C}$	
$dV/dt$	Critical rate of rise of reverse voltage			10000	V/ $\mu\text{s}$	

1.  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$  condition to avoid thermal runaway for a diode on its own heatsink

**Table 3. Thermal resistance**

Symbol	Parameter			Value	Unit
$R_{th(j-c)}$	Junction to case	TO-220AB / I <sup>2</sup> PAK	Per diode	2.2	$^\circ\text{C/W}$
			Total	1.3	
$R_{th(c)}$			Coupling	0.3	
$R_{th(j-c)}$	Junction to case	TO-220FPAB	Per diode	4.5	$^\circ\text{C/W}$
			Total	3.5	
$R_{th(c)}$			Coupling	2.5	

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_{j(\text{diode } 1)} = P_{(\text{diode } 1)} \times R_{th(j-c)(\text{Per diode})} + P_{(\text{diode } 2)} \times R_{th(c)}$$

**Table 4. Static electrical characteristics (per diode)**

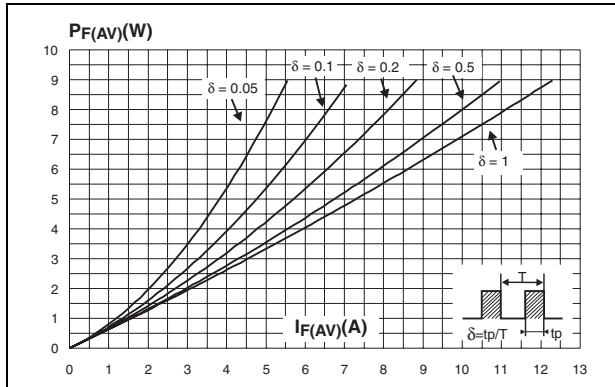
Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
$I_R$ <sup>(1)</sup>	Reverse leakage current	$T_j = 25\text{ }^\circ\text{C}$	$V_R = V_{RRM}$			3.5	$\mu\text{A}$
		$T_j = 125\text{ }^\circ\text{C}$			1.3	4.5	mA
$V_F$ <sup>(2)</sup>	Forward voltage drop	$T_j = 25\text{ }^\circ\text{C}$	$I_F = 5\text{ A}$			0.73	V
		$T_j = 125\text{ }^\circ\text{C}$			0.57	0.61	
		$T_j = 25\text{ }^\circ\text{C}$	$I_F = 10\text{ A}$			0.85	
		$T_j = 125\text{ }^\circ\text{C}$			0.66	0.71	
		$T_j = 25\text{ }^\circ\text{C}$	$I_F = 20\text{ A}$			0.94	
		$T_j = 125\text{ }^\circ\text{C}$			0.74	0.80	

1. Pulse test:  $t_p = 5\text{ ms}$ ,  $\delta < 2\%$

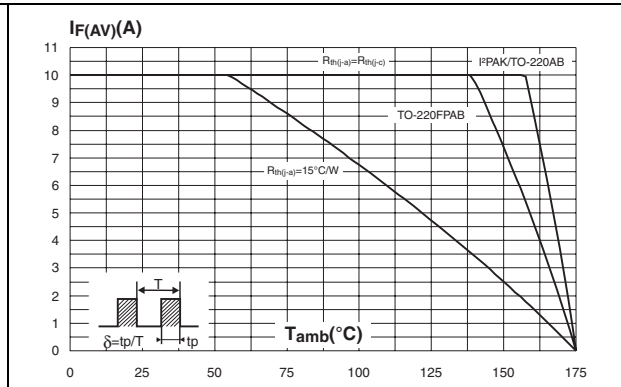
2. Pulse test:  $t_p = 380\text{ }\mu\text{s}$ ,  $\delta < 2\%$

To evaluate the conduction losses use the following equation:  $P = 0.62 \times I_{F(AV)} + 0.009 I_{F(RMS)}^2$

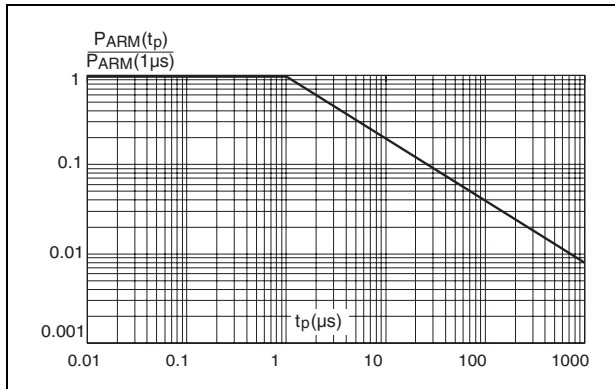
**Figure 1. Average forward power dissipation versus average forward current (per diode)**



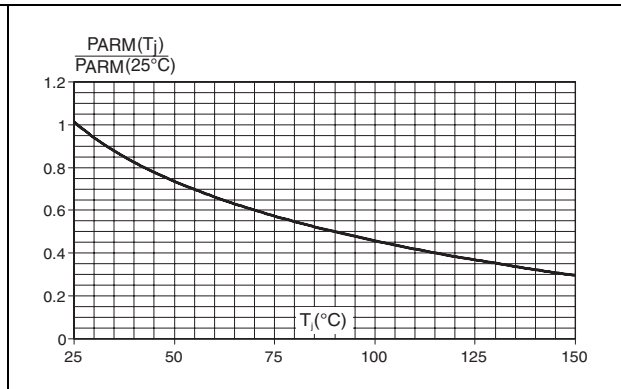
**Figure 2. Average forward current versus ambient temperature (delta = 0.5, per diode)**



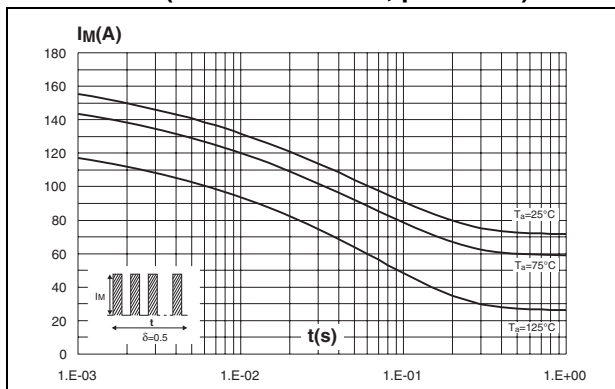
**Figure 3. Normalized avalanche power derating versus pulse duration**



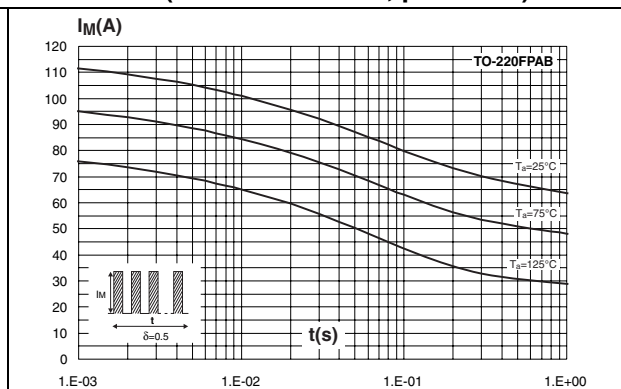
**Figure 4. Normalized avalanche power derating versus junction temperature**



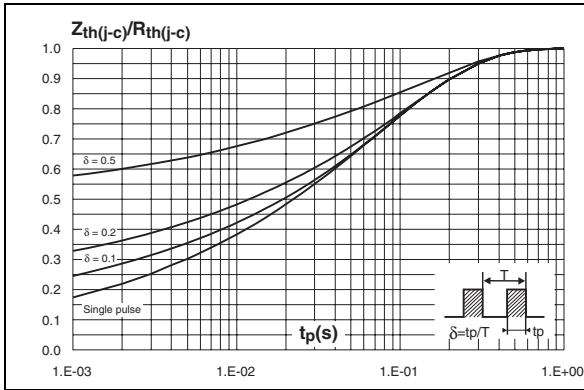
**Figure 5. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)**



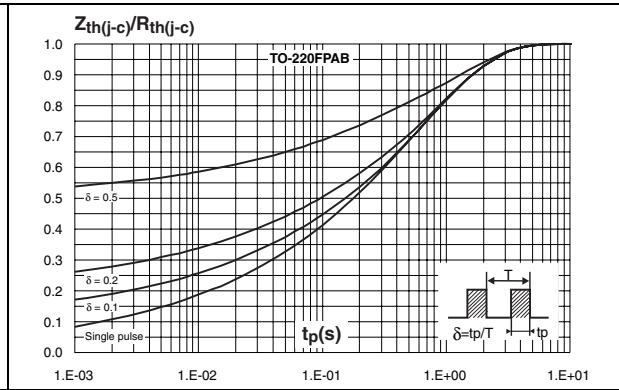
**Figure 6. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)**



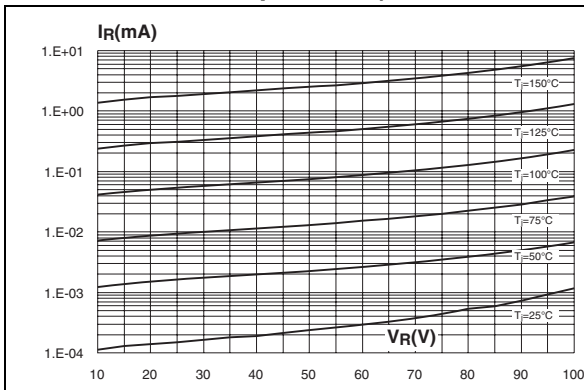
**Figure 7. Relative variation of thermal impedance junction to case versus pulse duration (per diode)**



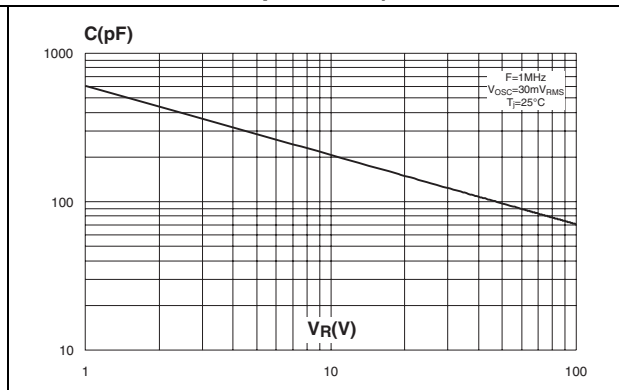
**Figure 8. Relative variation of thermal impedance junction to case versus pulse duration (per diode) (TO-220FPAB)**



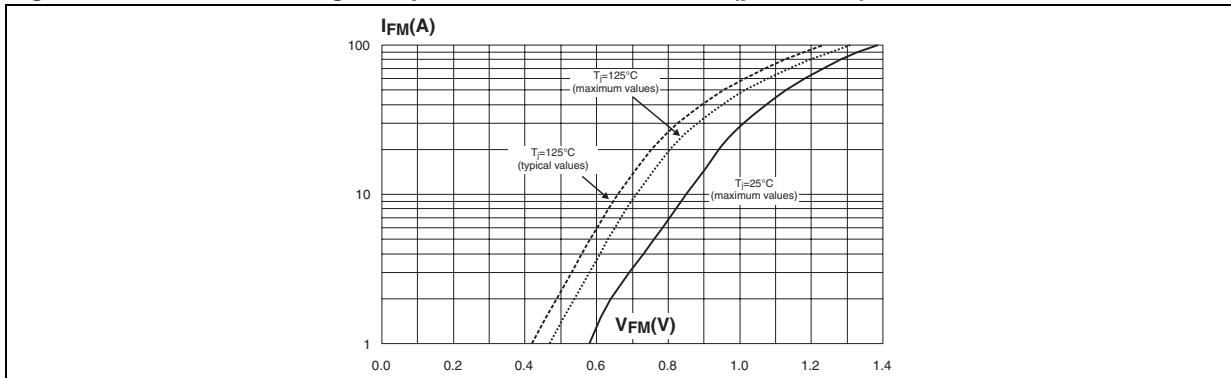
**Figure 9. Reverse leakage current versus reverse voltage applied (typical values, per diode)**



**Figure 10. Junction capacitance versus reverse voltage applied (typical values, per diode)**



**Figure 11. Forward voltage drop versus forward current (per diode)**



## 2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.4 to 0.6 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

**Table 5. TO-220FPAB dimensions**

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.4	4.6	0.173	0.181
B	2.5	2.7	0.098	0.106
D	2.5	2.75	0.098	0.108
E	0.45	0.70	0.018	0.027
F	0.75	1	0.030	0.039
F1	1.15	1.70	0.045	0.067
F2	1.15	1.70	0.045	0.067
G	4.95	5.20	0.195	0.205
G1	2.4	2.7	0.094	0.106
H	10	10.4	0.393	0.409
L2	16 Typ.		0.63 Typ.	
L3	28.6	30.6	1.126	1.205
L4	9.8	10.6	0.386	0.417
L5	2.9	3.6	0.114	0.142
L6	15.9	16.4	0.626	0.646
L7	9.00	9.30	0.354	0.366
Dia.	3.00	3.20	0.118	0.126

Table 6. I<sup>2</sup>PAK dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.40	2.72	0.094	0.107
b	0.61	0.88	0.024	0.035
b1	1.14	1.70	0.044	0.067
c	0.49	0.70	0.019	0.028
c2	1.23	1.32	0.048	0.052
D	8.95	9.35	0.352	0.368
e	2.40	2.70	0.094	0.106
e1	4.95	5.15	0.195	0.203
E	10	10.40	0.394	0.409
L	13	14	0.512	0.551
L1	3.50	3.93	0.138	0.155
L2	1.27	1.40	0.050	0.055

Table 7. TO-220AB dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
F2	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
G1	2.40	2.70	0.094	0.106
H2	10	10.40	0.393	0.409
L2	16.4 typ.		0.645 typ.	
L4	13	14	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam.	3.75	3.85	0.147	0.151

### 3 Ordering information

**Table 8. Ordering information**

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS20S100CT	STPS20S100CT	TO-220AB	2.20 g	50	Tube
STPS20S100CFP	STPS20S100CFP	TO-220FPAB	2 g	50	Tube
STPS20S100CR	STPS20S100CR	I <sup>2</sup> PAK	1.49 g	50	Tube

### 4 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
16-Mar-2005	1	First issue.
03-Feb-2010	2	Added cathode indicator K to illustration of TO-220AB on cover page. Changed parameter in <a href="#">Table 2</a> from “ RMS forward voltage “ to “ Forward rms current “.



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